N-Channel Enhancement-Mode Vertical DMOS FETs

Features

- Free from secondary breakdown
- Low power drive requirement
- Ease of paralleling
- Low C_{ISS} and fast switching speeds
- High input impedance and high gain

Applications

- Motor controls
- Converters
- Amplifiers
- Switches
- Power supply circuits
- Drivers (relays, hammers, solenoids, lamps, memories, displays, bipolar transistors, etc.)

General Description

The Supertex VN2106 is an enhancement-mode (normally-off) transistor that utilizes a vertical DMOS structure and Supertex's well-proven silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors, and the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally-induced secondary breakdown.

Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

Ordering Information

Device	Package Option	BV_{DSS}/BV_{DGS} (V)	$R_{DS(ON)}$ (max) (Ω)
	TO-92		
VN2106	VN2106N3-G	60	4.0

-G indicates package is RoHS compliant ('Green')

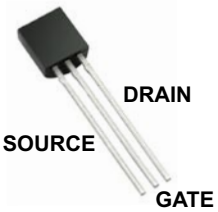
Absolute Maximum Ratings

Parameter	Value
Drain-to-Source voltage	BV_{DSS}
Drain-to-Gate voltage	BV_{DGS}
Gate-to-Source voltage	±20V
Operating and storage temperature	-55°C to +150°C
Soldering temperature*	+300°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

* *Distance of 1.6mm from case for 10 seconds.*

Pin Configuration



TO-92 (N3)

Product Marking

YY = Year Sealed
WW = Week Sealed
_____ = "Green" Packaging

Package may or may not include the following marks: Si or

TO-92 (N3)

Thermal Characteristics

Package	I_D (continuous)† (mA)	I_D (pulsed) (A)	Power Dissipation @T_C = 25°C (W)	θ_{jc} (°C/W)	θ_{ja} (°C/W)	I_{DR}† (mA)	I_{DRM} (A)
TO-92	300	1.0	1.0	125	170	300	1.0

Notes:

† I_D *(continuous) is limited by max rated* T_j.

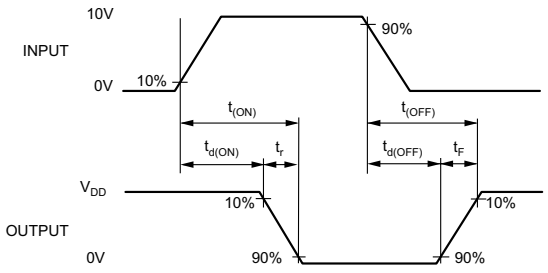
Electrical Characteristics *(T_A = 25°C unless otherwise specified)*

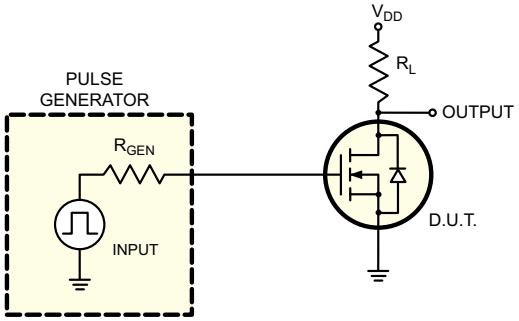
Sym	Parameter	Min	Typ	Max	Units	Conditions
BV_{DSS}	Drain-to-source breakdown voltage	60	-	-	V	V_{GS} = 0V, I_D = 1.0mA
$V_{GS(th)}$	Gate threshold voltage	0.8	-	2.4	V	V_{GS} = V_{DS}, I_D = 1.0mA
$\Delta V_{GS(th)}$	Change in $V_{GS(th)}$ with temperature	-	-3.8	-5.5	mV/°C	V_{GS} = V_{DS}, I_D = 1.0mA
I_{GSS}	Gate body leakage current	-	0.1	100	nA	V_{GS} = ±20V, V_{DS} = 0V
I_{DSS}	Zero gate voltage drain current	-	-	1.0	µA	V_{GS} = 0V, V_{DS} = Max Rating
		-	-	100		V_{DS} = 0.8 Max Rating, V_{GS} = 0V, T_A = 125°C
$I_{D(ON)}$	On-state drain current	0.6	-	-	A	V_{GS} = 10V, V_{DS} = 25V
$R_{DS(ON)}$	Static drain-to-source on-state resistance	-	4.5	6.0	Ω	V_{GS} = 5.0V, I_D = 75mA
		-	3.0	4.0		V_{GS} = 10V, I_D = 500mA
$\Delta R_{DS(ON)}$	Change in $R_{DS(ON)}$ with temperature	-	0.7	1.0	%/°C	V_{GS} = 10V, I_D = 500mA
G_{FS}	Forward transconductance	150	400	-	mmho	V_{DS} = 25V, I_D = 500mA
C_{ISS}	Input capacitance	-	35	50	pF	V_{GS} = 0V, V_{DS} = 25V, f = 1.0MHz
C_{OSS}	Common source output capacitance	-	13	25		
C_{RSS}	Reverse transfer capacitance	-	4.0	5.0		
$t_{d(ON)}$	Turn-on delay time	-	3.0	5.0	ns	V_{DD} = 25V, I_D = 600mA, R_{GEN} = 25Ω
t_r	Rise time	-	5.0	8.0		
$t_{d(OFF)}$	Turn-off delay time	-	6.0	9.0		
t_f	Fall time	-	5.0	8.0		
V_{SD}	Diode forward voltage drop	-	1.2	1.8	V	V_{GS} = 0V, I_{SD} = 600mA
t_{rr}	Reverse recovery time	-	400	-	ns	V_{GS} = 0V, I_{SD} = 600mA

Notes:

1. *All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: 300µs pulse, 2% duty cycle.)*
2. *All A.C. parameters sample tested.*

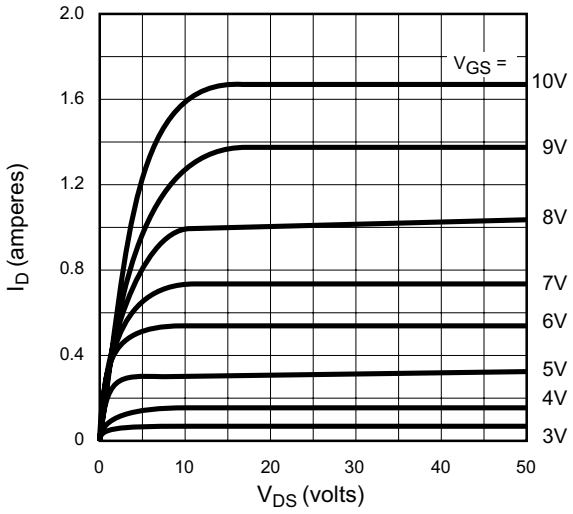
Switching Waveforms and Test Circuit



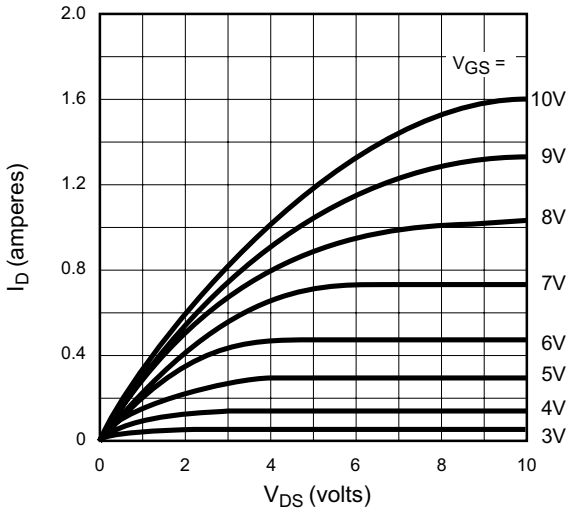


Typical Performance Curves

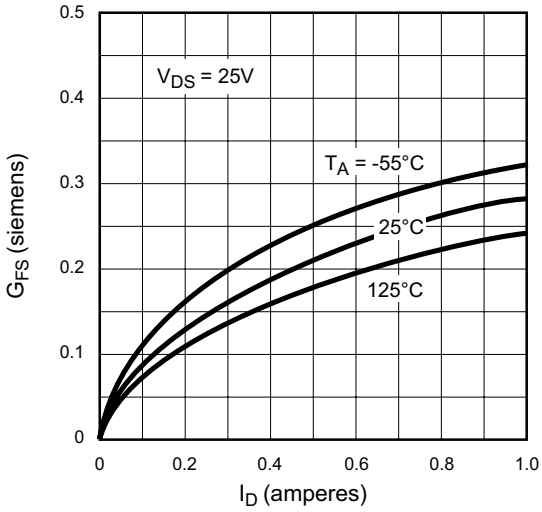
Output Characteristics



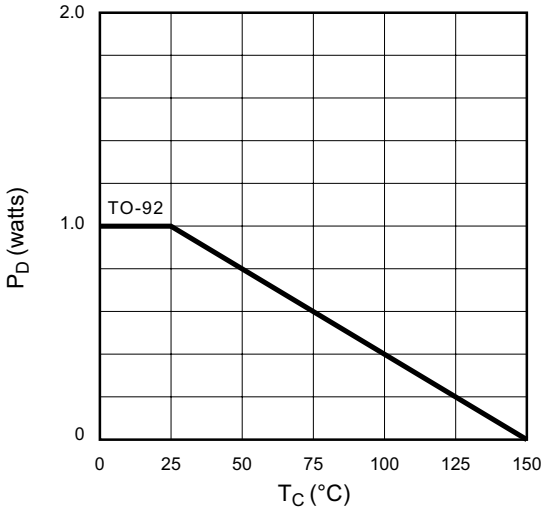
Saturation Characteristics



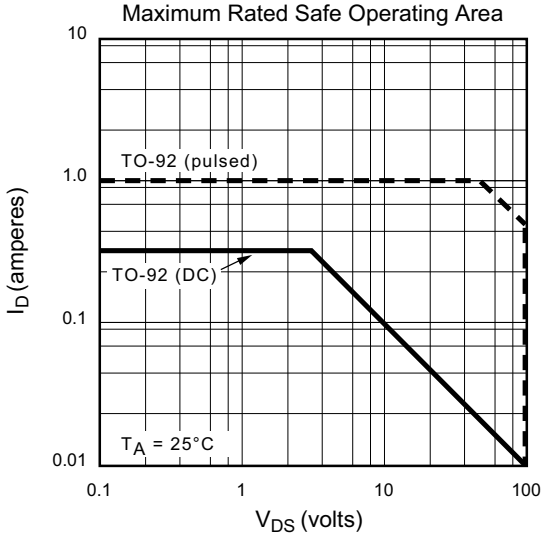
Transconductance vs. Drain Current



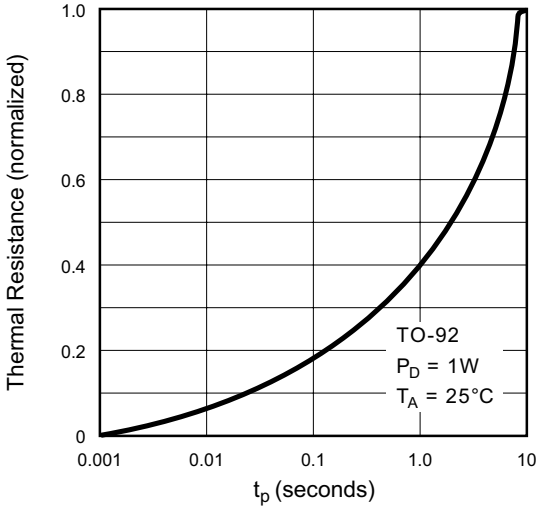
Power Dissipation vs. Case Temperature



Maximum Rated Safe Operating Area

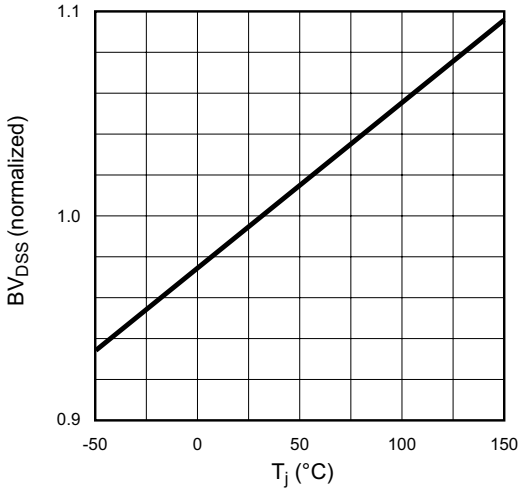


Thermal Response Characteristics

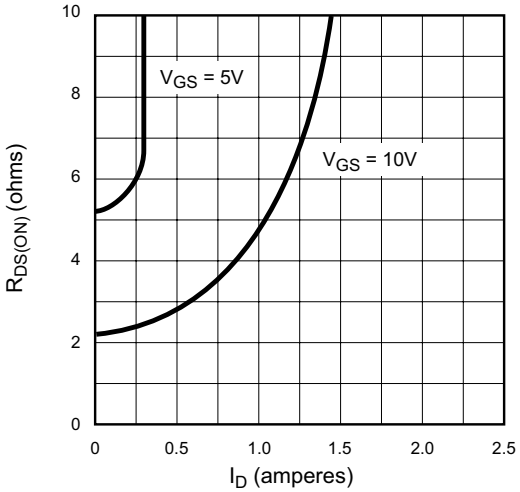


Typical Performance Curves *(cont.)*

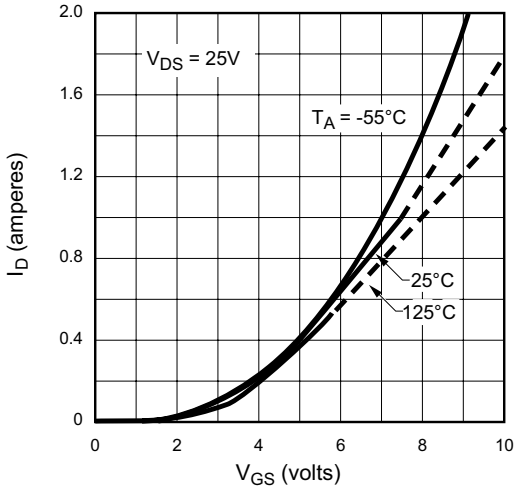
BV$_{DSS}$ Variation with Temperature



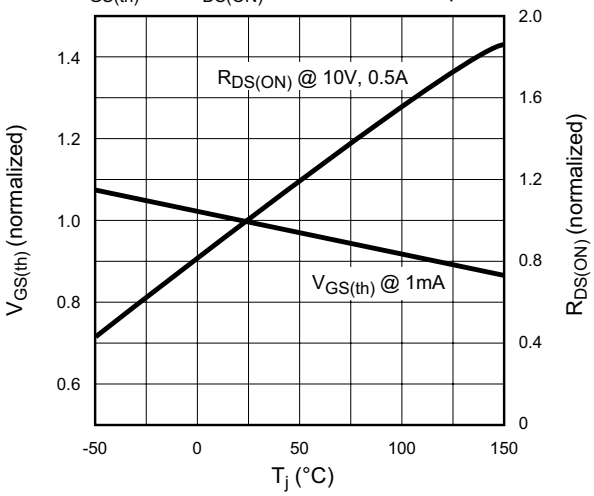
On-Resistance vs. Drain Current



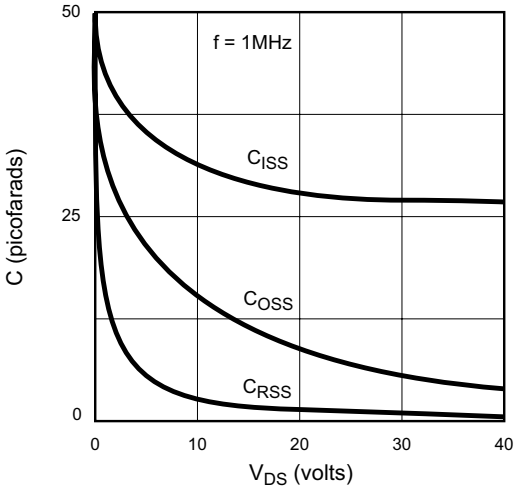
Transfer Characteristics



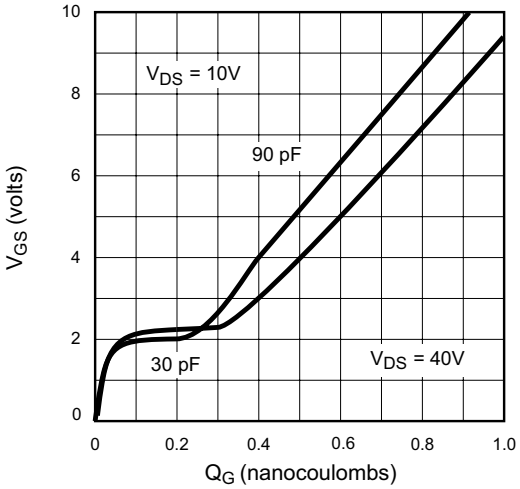
VGS(th) and RDS(ON) Variation with Temperature



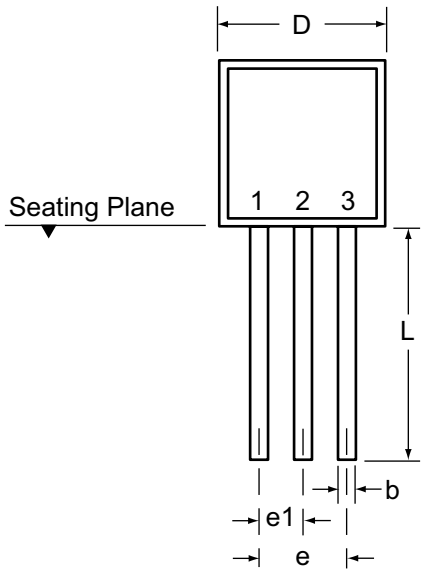
Capacitance vs. Drain-to-Source Voltage



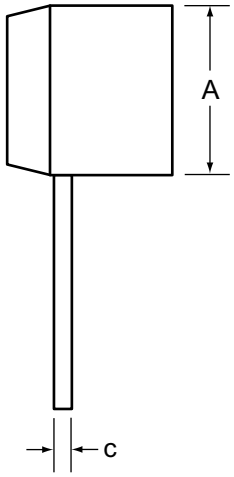
Gate Drive Dynamic Characteristics



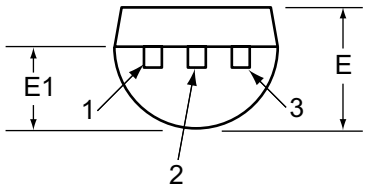
3-Lead TO-92 Package Outline (N3)



Front View



Side View



Bottom View

Symbol		A	b	c	D	E	E1	e	e1	L
Dimensions (inches)	MIN	.170	.014†	.014†	.175	.125	.080	.095	.045	.500
	NOM	-	-	-	-	-	-	-	-	-
	MAX	.210	.022†	.022†	.205	.165	.105	.105	.055	.610*

JEDEC Registration TO-92.
** This dimension is not specified in the original JEDEC drawing. The value listed is for reference only.*
† This dimension is a non-JEDEC dimension.
Drawings not to scale.
***Supertex Doc.#:** DSPD-3TO92N3, Version D080408.*

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to http://www.supertex.com/packaging.html.)

Supertex inc. does not recommend the use of its products in life support applications, and will not knowingly sell them for use in such applications unless it receives an adequate "product liability indemnification insurance agreement." **Supertex inc.** does not assume responsibility for use of devices described, and limits its liability to the replacement of the devices determined defective due to workmanship. No responsibility is assumed for possible omissions and inaccuracies. Circuitry and specifications are subject to change without notice. For the latest product specifications refer to the **Supertex inc.** website: http//www.supertex.com.

©2008 Supertex inc. All rights reserved. Unauthorized use or reproduction is prohibited.

Supertex inc.
1235 Bordeaux Drive, Sunnyvale, CA 94089
Tel: 408-222-8888
www.supertex.com

Общество с ограниченной ответственностью «МосЧип» ИНН 7719860671 / КПП 771901001
Адрес: 105318, г.Москва, ул.Щербаковская д.3, офис 1107

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

http://moschip.ru/get-element

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:
moschip.ru
moschip.ru_4
moschip.ru_6
moschip.ru_9